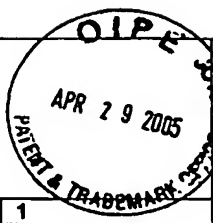


Substitute form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 1



Complete if Known

Application Number	10/698,170
Filing Date	October 30, 2003
First Named Inventor	Sei-Hyung Ryu
Group Art Unit	2811
Examiner Name	Tran, Long K.
Attorney Docket Number	5308-279

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
LT	1	6,303,508	B1	Alok	10/2001
	2	6,297,100	B1	Kumar et al.	10/2001
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		Office	Number	Kind Code (if known)			
LT	20	WO	97/08754			03/1997	

OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
LT	21	Palmour et al. "SiC Device Technology: Remaining Issues," Diamond and Related Materials. vol. 6, 1997, pp. 1400-1404.	
LT	22	Rao et al. "P-N Junction Formation in 6H-SiC by Acceptor Implantation into N-Type Substrate," Nuclear Instruments and Methods in Physics Research B. vol. 106, 1995, pp. 333-338.	
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Examiner Signature

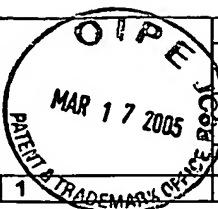
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Date Considered

05/05/2006

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Substitute form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/698,170
		Filing Date	October 30, 2003
		First Named Inventor	Sei-Hyung Ryu
		Group Art Unit	2811
		Examiner Name	Tran, Long K.
Sheet 1 of 1	Attorney Docket Number	5308-279	



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Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
LT	1.	US-6,759,684		Fukuda et al.	07-06-2004
	2.	US-6,653,659		Ryu et al.	11-25-2003
	3.	US-6,573,534		Kumar et al.	06-03-2003
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	17.	US-2002/0047125	A1	Fukuda et al.	04-25-2002

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LT	18.	EPO	EP 1 204 145	A2	Matsushita Electric Industrial Co., Ltd.	05-08-2002	
LT	19.	PCT	WO 98/02916		ABB Research, Ltd.	01-22-1998	

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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			
LT	20.	United States Patent Application Serial No. 10/686,795, "Methods of Forming Power Semiconductor Devices Using Boule-Grown Silicon Carbide Drift Layers and Power Semiconductor Devices Formed Thereby," filed October 16, 2003 (Attorney Docket No. 5308-286).			

Examiner Signature	/Long Tran/	Date Considered	05/05/2006
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number: 5308-279		Serial No.: 10/698,170	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Sei-Hyung Ryu			
				Filing Date: October 30, 2003		Group 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
LT	1.	6,204,135	03/20/2001	Peters et al.	438	301	
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		Document Number	Date	Country	Class	Subclass	Translation Yes No
LT	2.	DE 198 32 329	2/4/1999	Germany	H01L	21/334	
LT	3.	WO 01/78134	10/18/2001	PCT	H01L	21/76	
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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Sei-Hyung Ryu			
				Filing Date: October 30, 2003		Group 281	

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LT	1.	6,429,041	08/06/2002	Ryu et al.	438	105	

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LT	2.	JP 03034466	02/14/1991	Japan			Abstract
LT	3.	JP 01117363	05/10/1989	Japan			Abstract
LT	4.	EP 1058317 A2	12/06/2000	EPO			
LT	5.	DE 19809554 A1	09/10/1998	Germany			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
LT	6.	Copy of International Search Report for PCT/US03/38490 mailed 08/05/2004

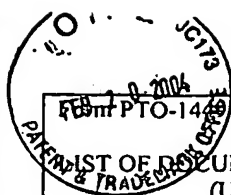
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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicant: Sei-Hyung Ryu	
		Filing Date: October 30, 2003	GAU: 2811

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	2	6,316,791	11/13/01	Schorner et al.	257	77	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	5,877,045	3/2/99	Kapoor	438	151	
	5	5,739,564	4/14/98	Kosa et al.	257	298	
	6	5,587,870	12/24/96	Anderson et al.	361	313	
	7	5,479,316	12/26/95	Smrtic et al.	361	322	
	8	2002/0102358	8/1/02	Das et al.	472	376.2	10/26/01
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LT	11	WO99/63591	12/9/99	PCT			
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LT	14	Bhatnagar et al. "Comparison of 6H-SiC, 3C-SiC, and Si for Power Devices," <i>IEEE Transactions on Electron Devices</i> , Vol. 40, No. 3, March 1993, pp. 645-55.
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	17	United States Provisional Patent Application Serial No. 60/294,307
	18	United States Patent Application Serial No. 10/422,130
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Examiner:

/Long Tran/

Date Considered: 05/05/2006

Examiner:

Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Attorney Docket Number: 5308-279		Serial No.: To Be Assigned <div style="text-align: right; font-size: 1.2em;">10/698170</div>	
				Applicants: Sei-Hyung Ryu			
				Filing Date: Concurrently Herewith		Group Unknown 2878	

U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
UKT	1	6,593,620	7/15/03	Hsieh et al.	257	335	
	2	6,455,892	9/02	Okuno	257	77	
	3	6,344,663 B1	2/5/02	Slater, Jr. et al.	257	77	
	4	6,297,172	10/2/01	Kashiwagi	438	773	
	5	6,246,076 B1	6/12/01	Lipkin et al.	257	77	
	6	6,239,463	5/29/01	Williams et al.	257	328	
	7	6,238,967 B1	5/29/01	Shiho et al.	438	244	
	8	6,221,700	4/24/01	Okuno et al.	438	151	
	9	6,211,035	4/01	Moise et al.	438	396	
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	13	6,136,728	10/24/00	Wang			
	14	6,117,735	9/12/00	Ueno	438	268	
	15	6,107,142	8/22/00	Suvorov et al.	438	285	
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	17	6,096,607	8/1/00	Ueno	438	522	
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W	22	6,025,608	2/15/00	Harris et al.	257	77	
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					Applicants: Sei-Hyung Ryu			
					Filing Date: Concurrently Herewith			Group Unknown <div style="font-size: 1.2em; font-family: cursive;">2878</div>

<div style="font-size: 1.5em; font-family: cursive;">W</div>	28	5,837,572	11/17/98	Gardner et al.	438	199	
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	30	5,726,463	3/10/98	Brown et al.	257	77	
	31	5,510,630	4/23/96	Agarwal	257	77	
	32	5,506,421	4-9-96	Palmour	257	77	
	33	5,184,199	2/2/93	Fujii et al.	29	10	
	34	5,170,455	12/8/92	Goossen et al.	385	89	
	35	5,170,231	12/92	Fujii et al.	257	77	
	36	4,875,083	10/17/89	Palmour	357	23.6	
	37	4,466,172	8/21/84	Batra	29	571	
	38	3,924,024	12/2/75	Naber et al.	427	95	
	39	2002/0072247	6/13/02	Lipkin et al.	438	767	
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		DE 198 09 554	9/10/98	Germany			Abstract
		DE 19900171	12/26/00	Germany			Abstract
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		JP 08264766	10/11/96	Japan			Abstract
		JP 09205202	8/5/97	Japan			Abstract
		JP 11191559	7/13/99	Japan			Abstract
		JP 11238742	8/31/99	Japan			Abstract
		JP 11261061	9/24/99	Japan			Abstract
		JP 11266017	9/28/99	Japan			Abstract
		JP 11274487	10/8/99	Japan			Abstract
		JP 2000049167	2/18/00	Japan			Abstract
		JP 2000082812	3/21/00	Japan			Abstract

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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)					Applicants: Sei-Hyung Ryu			
					Filing Date: Concurrently Herewith			Group Unknown <i>2828</i>
<i>UET</i>	55	JP 2000106371	4/11/01	Japan				Abstract
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<i>UET</i>	58	WO 97/39485	10/23/97	PCT				
59 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
<i>UET</i>	59	A.K. Agarwal, J.B. Casady, L.B. Rowland, W.F. Valek, and C.D. Brandt, "1400 V 4H-SiC Power MOSFET's," <i>Materials Science Forum</i> Vols. 264-268, pp.989-992, 1998.						
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		Applicants: Sei-Hyung Ryu	
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LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Sei-Hyung Ryu	
		Filing Date: Concurrently Herewith	Group Unknown 28 18
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